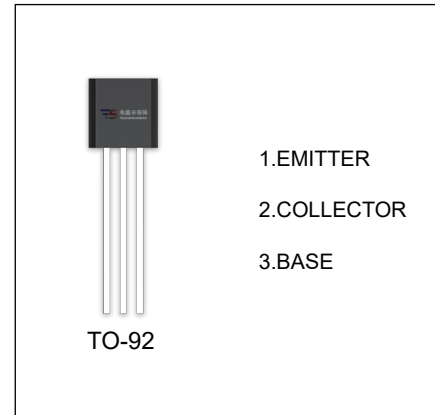


2SA1980 TRANSISTOR (PNP)

FEATURES

- Low Collector Saturation Voltage: $V_{CE(sat)} = -0.3V(\text{Max.})$
- Low Output Capacitance : $C_{ob} = 4pF$ (Typ.)
- Complementary Pair with 2SC5343



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2SA1980	TO-92	Bulk	1000pcs/Bag
2SA1980-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.15	A
P_D	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	200	$^{\circ}\text{C} / \text{W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

$T_a=25\text{ }^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}, I_E=0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10\text{mA}, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-50\text{V}, I_E=0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{EB}=-5\text{V}, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-6\text{V}, I_C=-2\text{mA}$	70		700	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100\text{mA}, I_B=-10\text{mA}$			-0.3	V
Transition frequency	f_T	$V_{CE}=-10\text{V}, I_C=-1\text{mA}$	80			MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		4	7	pF
Noise figure	NF	$V_{CE}=-6\text{V}, I_C=-0.1\text{mA}, f=1\text{KHz}, R_S=10\text{K}\Omega$			10	dB

CLASSIFICATION OF h_{FE}

Rank	O	Y	G	L
Range	70-140	120-240	200-400	300-700